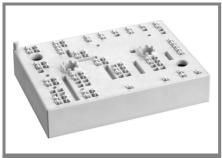
## SKiiP 35NAB126V1



MiniSKiiP® 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter **SKIIP 35NAB126V1** 

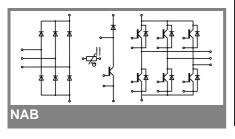
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## **Typical Applications**

- Inverter up to 28 kVA
- Typical motor power 15 kW

## **Remarks**

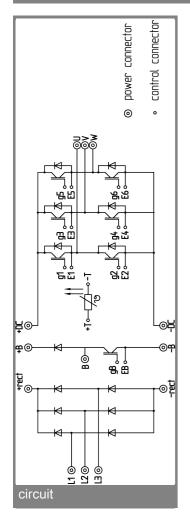
• V<sub>CEsat</sub> , V<sub>F</sub>= chip level value

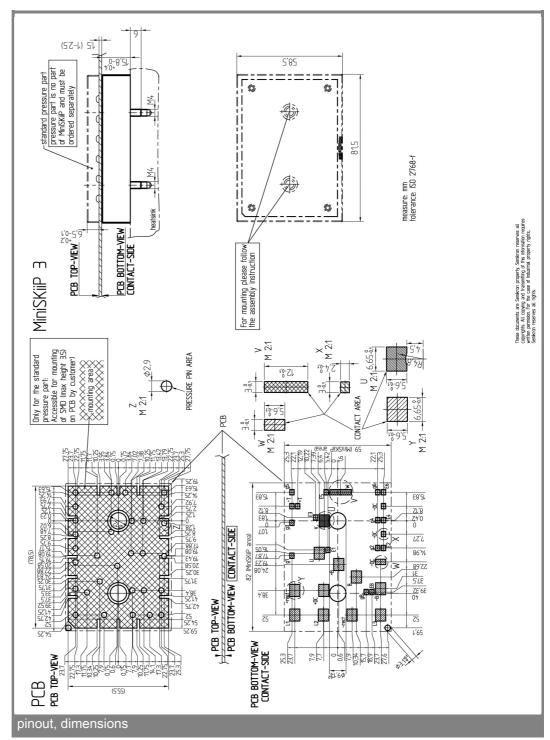


<b>Absolute Maximum Ratings</b> T <sub>s</sub> = 25 °C, unless otherwise specifie							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
$V_{CES}$		1200	V				
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	73 (55)	Α				
I <sub>CRM</sub>	$t_p \le 1 \text{ ms}$	100	Α				
$V_{GES}$		± 20	V				
T <sub>j</sub>		- 40 <b>+</b> 150	°C				
Diode - Inverter, Chopper							
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	62 (46)	Α				
I <sub>FRM</sub>	$t_p \le 1 \text{ ms}$	100	Α				
T <sub>j</sub>		- 40 <b>+</b> 150	°C				
Diode - Rectifier							
$V_{RRM}$		1600	V				
I <sub>F</sub>	$T_s = 70  ^{\circ}C$	61	Α				
I <sub>FSM</sub>	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_i = 25 ^\circ\text{C}$	700	Α				
i²t	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	2400	A²s				
T <sub>j</sub>		- 40 <b>+</b> 150	°C				
I <sub>tRMS</sub>	per power terminal (20 A / spring)	80	Α				
T <sub>stg</sub>	$T_{op} \le T_{stg}$	- 40 <b>+</b> 125	°C				
V <sub>isol</sub>	AC, 1 min.	2500	V				

Character	ristics	r <sub>s</sub> = 25 °C, unless otherwise specified							
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V <sub>CEsat</sub> V <sub>GE(th)</sub>	$I_{Cnom}$ = 50 A, $T_j$ = 25 (125) °C $V_{GE}$ = $V_{CE}$ , $I_C$ = 2 mA	5	1,7 (2) 5,8	2,1 (2,4) 6,5	V				
V <sub>CE(TO)</sub>	T <sub>i</sub> = 25 (125) °C		1 (0,9)	1,2 (1,1)	V				
r <sub>T</sub>	T <sub>i</sub> = 25 (125) °C		14 (22)	18 (26)	mΩ				
C <sub>ies</sub>	$V'_{CE}$ = 25 V, $V_{GE}$ = 0 V, f = 1 MHz		3,7		nF				
C <sub>oes</sub>	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,8		nF				
C <sub>res</sub>	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,7		nF				
$R_{th(j-s)}$	per IGBT		0,55		K/W				
t <sub>d(on)</sub>	under following conditions		85		ns				
t <sub>r</sub>	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		30		ns				
t <sub>d(off)</sub>	$I_{Cnom} = 50 \text{ A}, T_j = 125^{\circ}\text{C}$		430		ns				
t <sub>f</sub>	$R_{Gon} = R_{Goff} = 12 \Omega$		90		ns				
E <sub>on</sub>	inductive load		6,5		mJ				
$E_{off}$			6,1		mJ				
Diode - Inverter, Chopper									
$V_F = V_{EC}$	I <sub>Fnom</sub> = 50 A, T <sub>j</sub> = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V				
$V_{(TO)}$	T <sub>j</sub> = 25 (125) °Ć		1 (0,8)	1,1 (0,9)	V				
r <sub>T</sub>	T <sub>j</sub> = 25 (125) °C		12 (16)	14 (18)	mΩ				
$R_{th(j-s)}$	per diode		1		K/W				
I <sub>RRM</sub>	under following conditions		71		Α				
$Q_{rr}$	I <sub>Fnom</sub> = 50 A, V <sub>R</sub> = 600 V		11,5		μC				
E <sub>rr</sub>	V <sub>GE</sub> = 0 V, T <sub>j</sub> = 125 °C		4,7		mJ				
	di <sub>F</sub> /dt = 1900 A/µs								
Diode - Rectifier									
$V_{F}$	I <sub>Fnom</sub> = 35 A, T <sub>i</sub> = 25 °C		1,1		V				
$V_{(TO)}$	T <sub>i</sub> = 150 °C		0,8		V				
r <sub>T</sub>	T <sub>j</sub> = 150 °C		11		mΩ				
$R_{th(j-s)}$	per diode		0,9		K/W				
	ure Sensor								
R <sub>ts</sub>	3 %, T <sub>r</sub> = 25 (100) °C		1000(1670)		Ω				
Mechanical Data									
w			95		g				
$M_s$	Mounting torque	2		2,5	Nm				

## SKiiP 35NAB126V1





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.